12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20260609002.1
Qualification of AIZU/RFAB as an additional Fab site and TI Chengdu as additional Assembly site options for select devices
Change Notification / Sample Request

Date: June 15, 2026
To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

TI values customer engagement and feedback related to TI changes. Customers should contact TI if there are questions or concerns regarding a change notification.

Sincerely,

Change Management Team
SC Business Services

20260609002.1
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
INA212AIDCKR	INA212AIDCKR
INA212AIDCKT	INA212AIDCKT

Technical details of this Product Change follow on the next page(s).

PCN Number:	20260609002.1	PCN Date:	June 15, 2026
Title:	Qualification of AIZU/RFAB as an additional Fab site and TI Chengdu as additional Assembly site options for select devices		
Customer Contact:	Change Management Team	Dept:	Quality Services
Proposed 1st Ship Date:	September 13, 2026	Sample requests accepted until:	August 14, 2026*

*Sample requests received after August 14, 2026 will not be supported.

Change Type:

☒	Assembly Site	☐	Design	☐	Wafer Bump Material
☒	Assembly Process	☐	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☒	Wafer Fab Site
☐	Mechanical Specification	☐	Test Site	☒	Wafer Fab Material
☒	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of AIZU/RFAB as an additional Fab site option & TI Chengdu as additional Assembly site options for the devices listed below.

Current Fab Site			Additional Fab site		
Current Fab Site	**Process**	**Wafer Diameter**	**Additional Fab site**	**Process**	**Wafer Diameter**
DMOS5	50HPA07	200mm	AIZU/RFAB	50HPA07	300mm

Construction differences are as follows:

	Current Site				Additional Site
Assembly Site	**HFTF**	**HNA**	**TFME**	**UTL2**	**CDAT**
Wire bond Diam/type	1.0mil Au	1.0mil Au	1.0mil Au	1.0mil Au	0.8mil Cu
Mount compound	SID#A-09	SID#A-09	SID#A-09	SID#PZ0037	4226215
Mold compound	SID#R-27	SID#450179	SID#R-07	SID#CZ0096	4222198

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

These devices include new die based on existing schematics in a larger diameter wafer fab with or without a die shrink. Review the Standard Data Packet for more details on the changes.

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin	Chip Site Country	Chip Site City

	Code (20L)	Code (21L)	
DMOS5	DM5	USA	Dallas
AIZU	**CU2**	**JPN**	**Aizuwakamatsu-shi**
RFAB	**RFB**	**USA**	**Richardson**

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
HFTF	HFT	CHN	Hefei
HNA	HNT	THA	Ayutthaya
TFME	NFM	CHN	Chongchuan
UTL2	NS2	THA	Bangpakong
TI Chengdu	**CDA**	**CHN**	**Chengdu**

Sample product shipping label (not actual product label):

Product Affected:

INA211AIDCKT	INA212AIDCKR	INA212AIDCKT

Qualification Report

INA210_INA199_COMMERCIAL AIZU
Approve Date 20-DECEMBER -2024

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: INA214AIDCKR	QBS Package, Process, Product Reference: INA210BQDCKRTL
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	1/77/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	1/77/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	1/45/0
PD	C4	Physical Dimensions	Cpk>1.67	-	-	1/10/0
ESD	E2	ESD CDM	-	250 Volts	1/3/0	-
ESD	E2	ESD CDM	-	500 Volts	-	1/3/0
ESD	E2	ESD HBM	-	1000 Volts	1/3/0	-
ESD	E2	ESD HBM	-	2000 Volts	-	1/3/0
LU	E4	Latch-Up	Per JESD78	-	1/3/0	-
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	-
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	1/30/0

QBS: Qual By Similarity, also known as Generic Data
Qual Device INA214AIDCKR is qualified at MSL1 260C
Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Quality and Environmental data is available at TI's external Web site:
TI Qualification ID: R-CHG-2312-003

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 06-December-2024

Product Attributes

Attributes	Qual Device: INA210BQDCKRTL	QBS Process Reference: INA215AQDCKRQ1	QBS Package Reference: TPS3840PH30DBVRQ1	QBS Package Reference: LM74703QDDFRQ1	QBS Package Reference: TXS0101QDCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Power Management	Power Management	Logic
Wafer Fab Supplier	AIZU	AIZU	RFAB	RFAB	RFAB
Assembly Site	CDAT	TFME	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT	SOT	SOT
Package Designator	DCK	DCK	DBV	DDF	DCK
Pin Count	6	6	5	8	6

QBS: Qual By Similarity, also known as Generic Data
Qual Device INA210BQDCKRTL is qualified at MSL1 260C
Note 1: Qual device and affected devices in PCN have justification to use Package QBS references for HAST, AC/UHAST and TC-BP based on AEC-100J A1.3 assembly site and package attributes were qualified.
Note 2: Qual device and affected devices in PCN have justification to use Process QBS references for HTOL and ELFR based on AEC-100J A1.2 silicon wafer fab and process attributes were qualified. Group B tests purpose is for silicon defects, they do not get influenced by assembly site or BOM differences.
Note 3: Qual device and affected devices in PCN have justification to use SD QBS based on AEC-100J A1.3 leadframe attributes are qualified.
Note 4: One lot is allowed per AEC-Q100J A1.5.1 Multiple Sites - When the specific product or process attribute to be qualified or requalified will affect more than one wafer fab site or assembly site, a minimum of one lot of testing per affected site is required.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: INA210BQDCKRTL	QBS Process Reference: INA215AQDCKRQ1	QBS Package Reference: TPS3840PH30DBVRQ1	QBS Package Reference: LM74703QDDFRQ1	QBS Package Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	1/Pass Note 4	-	3/Pass	3/Pass	3/Pass
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0 Note 4	-	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0 Note 4	-	3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	Note 1	-	1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0 Note 4	-	3/135/0	1/45/0	3/135/0

Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	Note 2	3/231/0	3/231/0	-	1/77/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	Note 2	-	-	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	Note 2	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0 Note 4	-	3/30/0	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0 Note 4	-	-	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0 Note 4	-	-	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0 Note 4	-	-	-	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/
TI Qualification ID: R-CHG-2405-062

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS

Process” (for wafer fab process), “QBS Package” (for assembly process) and “QBS Product” (for product family).

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.